

# KA1M0280RB/KA1H0280RB

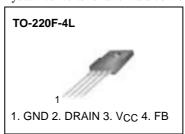
# Fairchild Power Switch(FPS)

#### **Features**

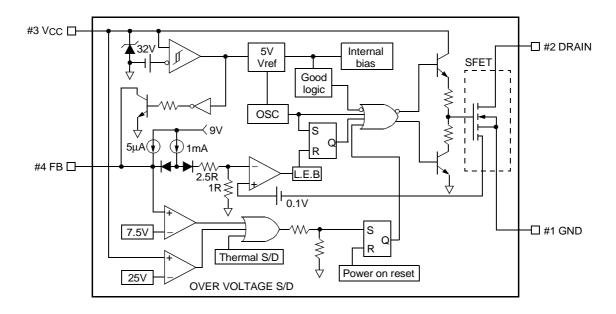
- Precision Fixed Operating Frequency
- KA1M0280RB (67kHz), KA1H0280RB (100kHz)
- Pulse by Pulse Over Current Limiting
- · Over Load Protection
- Over Voltage Protection (Min. 23V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- · Internal High Voltage Sense FET
- · Auto Restart

### **Description**

The Fairchild Power Switch(FPS) product family is specially designed for an off line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. PWM controller features integrated fixed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit. compared to discrete MOSFET and controller or RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a forward converter.



### **Internal Block Diagram**



# **Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Maximum Drain Voltage (1)	V <sub>D,MAX</sub>	800	V
Drain-Gate Voltage (RGS=1MΩ)	VDGR	800	V
Gate-Source (GND) Voltage	VGS	±30	V
Drain Current Pulsed (2)	IDM	8.0	ADC
Single Pulsed Avalanche Energy (3)	EAS	90	mJ
Avalanche Current (4)	IAS	8	A
Continuous Drain Current (TC=25°C)	ID	2.0	ADC
Continuous Drain Current (T <sub>C</sub> =100°C)	ΙD	1.3	ADC
Maximum Supply Voltage	VCC,MAX	30	V
Input Voltage Range	VFB	-0.3 to VSD	V
Total Power Dissipation	PD	35	W
	Darting	0.28	W/°C
Operating Ambient Temperature	TA	-25 to +85	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

#### Notes:

- 1.  $T_j = 25^{\circ}C$  to  $150^{\circ}C$
- 2. Repetitive rating: Pulse width limited by maximum junction temperature
- 3. L = 51mH, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , starting T<sub>j</sub> = 25 $^{\circ}$ C
- 4. L = 13 $\mu H$ , starting  $T_j = 25^{\circ} C$

# **Electrical Characteristics (SFET part)**

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	VGS=0V, ID=50μA	800	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS=Max., Rating, VGS=0V	-	-	50	μΑ
		V <sub>DS</sub> =0.8Max., Rating, V <sub>GS</sub> =0V, T <sub>C</sub> =125°C	-	-	200	μА
Static Drain-Source on Resistance (Note)	RDS(ON)	VGS=10V, ID=1.0A	-	5.6	7.0	Ω
Forward Transconductance (Note)	gfs	V <sub>DS</sub> =50V, I <sub>D</sub> =1.0A	1.5	2.5	-	S
Input Capacitance	Ciss		-	250	-	
Output Capacitance	Coss	VGS=0V, VDS=25V, f=1MHz	-	52	-	pF
Reverse Transfer Capacitance	Crss	1-11/11/2	-	25	-	
Turn on Delay Time	td(on)	VDD=0.5BVDSS, ID=2.0A (MOSFET switching time are essentially independent of operating temperature)	-	21	-	
Rise Time	tr		-	28	-	nS
Turn Off Delay Time	td(off)		-	77	-	113
Fall Time	tf		-	24	-	
Total Gate Charge (Gate-Source+Gate-Drain)	Qg	VGS=10V, ID=2.0A, VDS=0.5BVDSS (MOSFET switching time are essentially independent of operating temperature)	-	-	60	
Gate-Source Charge	Qgs		-	15	-	nC
Gate-Drain (Miller) Charge	Qgd		-	20	-	

#### Note:

1. Pulse test: Pulse width  $\leq 300 \mu S,$  duty cycle  $\leq 2\%$ 

$$2. S = \frac{1}{R}$$

# Electrical Characteristics (CONTROL part) (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit	
UVLO SECTION						•	
Start Threshold Voltage	VSTART	-	14	15	16	V	
Stop Threshold Voltage	VSTOP	After turn on	9	10	11	V	
OSCILLATOR SECTION	OSCILLATOR SECTION						
Initial Accuracy	Fosc	KA1M0280RB	61	67	73	- kHz	
		KA1H0280RB	90	100	110		
Frequency Change With Temperature (2)	ΔΕ/ΔΤ	-25°C ≤ Ta ≤ +85°C	-	±5	±10	%	
Maximum Duty Cycle	Dmax	KA1M0280RB	74	77	80	%	
		KA1H0280RB	64	67	70		
FEEDBACK SECTION							
Feedback Source Current	I <sub>FB</sub>	Ta=25°C, 0V ≤ Vfb ≤ 3V	0.7	0.9	1.1	mA	
Shutdown Feedback Voltage	VsD	-	6.9	7.5	8.1	V	
Shutdown Delay Current	Idelay	Ta=25°C, 5V ≤ Vfb ≤ VsD	4.0	5.0	6.0	μΑ	
REFERENCE SECTION							
Output Voltage (1)	Vref	Ta=25°C	4.80	5.00	5.20	V	
Temperature Stability (1)(2)	Vref/∆T	-25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C	
CURRENT LIMIT (SELF-PROTECTION)	SECTION					•	
Peak Current Limit	lover	Max. inductor current	1.05	1.2	1.35	Α	
PROTECTION SECTION						•	
Thermal Shutdown Temperature (Tj) (1)	T <sub>SD</sub>	-	140	160	-	°C	
Over Voltage Protection Voltage	Vovp	-	23	25	28	V	
TOTAL DEVICE SECTION							
Start-Up Current	ISTART	Vcc=14V	0.1	0.3	0.45	mA	
Operating Supply Current (Control Part Only)	lop	Ta=25°C	6	12	18	mA	
VCC Zener Voltage	Vz	ICC=20mA	30	32.5	35	V	

#### Note:

<sup>1.</sup> These parameters, although guaranteed, are not 100% tested in production

<sup>2.</sup> These parameters, although guaranteed, are tested in EDS (wafer test) process

### **Typical Performance Characteristics**

(These characteristic graphs are normalized at Ta=25°C)

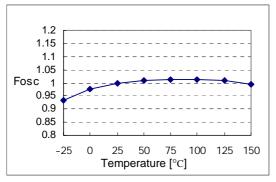


Figure 1. Operating Frequency

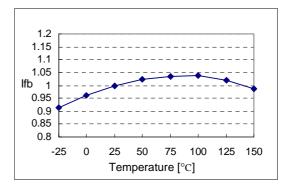


Figure 2. Feedback Source Current

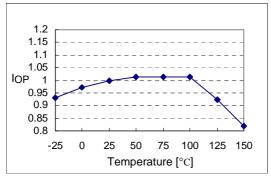


Figure 3. Operating Supply Current

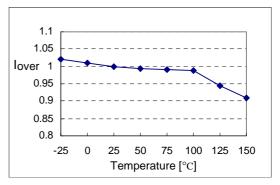


Figure 4. Peak Current Limit

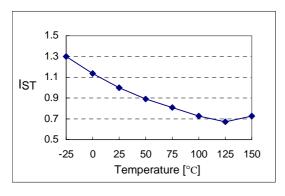


Figure 5. Start up Current

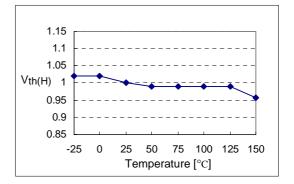


Figure 6. Start Threshold Voltage

### **Typical Performance Characteristics** (Continued)

(These characteristic graphs are normalized at Ta=25°C)

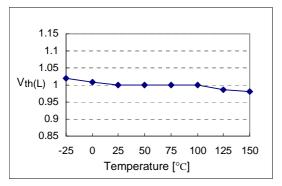


Figure 7. Stop Threshold Voltage

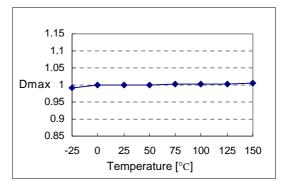


Figure 8. Maximum Duty Cycle

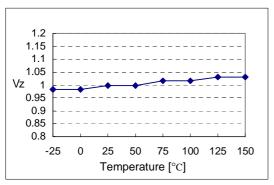


Figure 9. VCC Zener Voltage

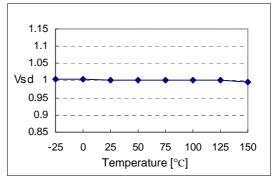


Figure 10. Shutdown Feedback Voltage

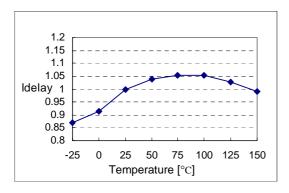


Figure 11. Shutdown Delay Current

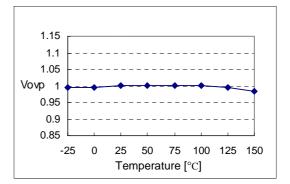


Figure 12. Over Voltage Protection

# **Typical Performance Characteristics** (Continued)

(These characteristic groups are normalized at Ta=25°C)

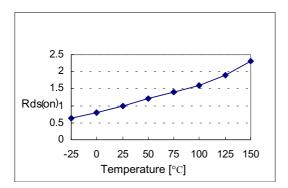
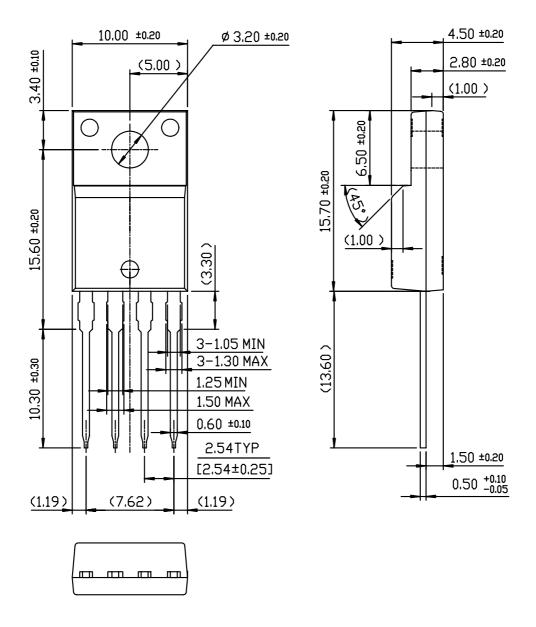


Figure 13. Static Drain-Source on Resistance

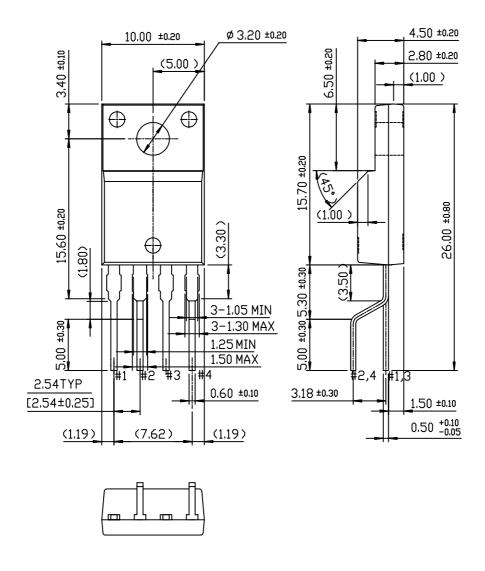
## **Package Dimensions**

TO-220F-4L



## Package Dimensions (Continued)

# TO-220F-4L(Forming)



### **Ordering Information**

Product Number	Package	Rating	Fosc		
KA1M0280RB-TU	TO-220F-4L	800V, 2A	67kHz		
KA1M0280RB-YDTU	TO-220F-4L(Forming)	600 V, ZA	07KHZ		
KA1H0280RB-TU	TO-220F-4L	800V, 2A	100kHz		
KA1H0280RB-YDTU	TO-220F-4L(Forming)	600 V, ZA	TOURHZ		

TU: Non Forming Type YDTU: Forming Type

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